



Product Overview

NTJD4105C: Small Signal MOSFET 20V 775mA 220 mOhm Complementary SC-88

For complete documentation, see the data sheet

Product Description

This complementary dual device was designed with a small package (2 x 2 mm) and low RDS(on) MOSFETs for minimum footprint and increased circuit efficiency. The low RDS(on) performance is particularly suited for single or dual cell Li-Ion battery supplied devices such as cell phones, media players, digital cameras, and PDAs.

Features

- Complementary N and P Channel Device
- Leading -8.0 V Trench for Low RDS(on) Performance
- ESD Protected Gate-ESD Rating: Class 1
- SC-88 Package for Small Footprint (2x2mm)
- Pb-Free Packages are Available

Applications

- DC-DC Conversion
- Load/Power Switching
- Single or Dual Cell Li-Ion Battery Supplied Devices
- Cell Phones, MP3s, Digital Cameras, and PDAs

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	V _{DS} (BR) Min (V)	V _{GS} Max (V)	V _{GS} (th) Max (V)	I _D Max (A)	P _D Max (W)	r _{DS(on)} Max @ V _{GS} = 2.5 V (m)	r _{DS(on)} Max @ V _{GS} = 4.5 V (m)	r _{DS(on)} Max @ V _{GS} = 10 V (m)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	Q _{gd} Typ @ V _{GS} = 4.5 V (nC)	Q _{rr} Typ (nC)	C _{iss} Typ (pF)	C _{oss} Typ (pF)	C _{rss} Typ (pF)	Package Type
NTJD4105CT1G	Pb-free Halide free	Active	Complementary	Dual	20	12	1.5	0.63	0.27	445	375		1.3		0.4		33	13	2.8	SC-88-6 / SC-70-6 / SOT-363-6
NTJD4105CT2G	Pb-free Halide free	Active	Complementary	Dual	20	12	1.5	0.63	0.27	445	375		1.3		0.4		33	13	2.8	SC-88-6 / SC-70-6 / SOT-363-6

For more information please contact your local sales support at www.onsemi.com

Created on: 7/11/2015